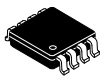
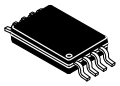
# EEPROM, Serial, 16-Kb I²C, Low Voltage Automotive Grade 1

# NV24C16LV



US8
U SUFFIX
CASE 493



TSSOP−8
DT SUFFIX
CASE 948AL

TSOP−5
SN SUFFIX
CASE 483

UDFN8
MUW3 SUFFIX
CASE 517DH

SOIC8
DW SUFFIX
CASE 751BD

## Description

The NV24C16LV are 16−Kb CMOS Serial EEPROM devices that operate at a minimum 1.7 V supply voltage. They are organized internally as 128 pages of 16 bytes each. All devices support the Standard (100 kHz), Fast (400 kHz) and Fast−Plus (1 MHz) I²C protocol.

Data is written by providing a starting address, then loading 1 to 16 contiguous bytes into a Page Write Buffer, and then writing all data to non−volatile memory in one internal write cycle. Data is read by providing a starting address and then shifting out data serially while automatically incrementing the internal address count.

External address pins make it possible to address up to one NV24C16 device on the same bus.

## Features

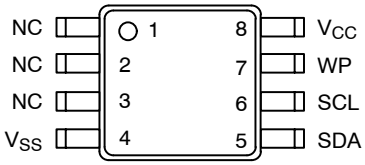
- Automotive AEC−Q100 Grade 1 (−40°C to +125°C) Qualified
- Supports Standard, Fast and Fast−Plus I²C Protocol
- 1.7 V to 5.5 V Supply Voltage Range
- 16−Byte Page Write Buffer
- Fast Write Time (4 ms max)
- Hardware Write Protection for Entire Memory
- Schmitt Triggers and Noise Suppression Filters on I²C Bus Inputs (SCL and SDA)
- Low power CMOS Technology
- More than 1,000,000 Program/Erase Cycles
- 100 Year Data Retention
- Automotive Grade 1 Temperature Range
- SOIC, TSSOP, US 8−Lead, TSOP−5 Lead and Wettable Flank UDFN 8−pad Packages
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

## ORDERING INFORMATION

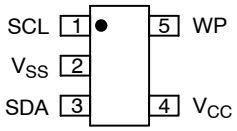
See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.

## PIN CONFIGURATION (SOIC−8,US−8,UDFN8 ,TSSOP−8)

NV24C16




## PIN CONFIGURATION (TSOP−5)

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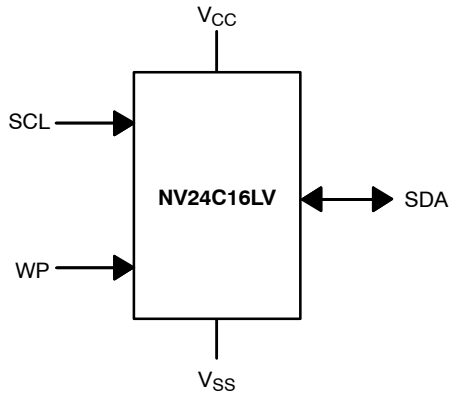



**Figure 1. Functional Symbol**

**Table 1. PIN FUNCTION**

| Pin Name | Function |
|---|---|
| SDA | Serial Data Input/Output |
| SCL | Serial Clock Input |
| WP | Write Protect Input |
| $V_{CC}$ | Power Supply |
| $V_{SS}$ | Ground |
| NC | No Connect |

**Table 2. ABSOLUTE MAXIMUM RATINGS**

| Parameters | Ratings | Units |
|---|---|---|
| Storage Temperature | −65 to +150 | °C |
| Voltage on any pin with respect to Ground (Note 1) | −0.5 to +6.5 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. During input transitions, voltage undershoot on any pin should not exceed −1 V for more than 20 ns. Voltage overshoot on pin WP should not exceed $V_{CC}$ + 1 V for more than 20 ns, while voltage on the $I^2C$ bus pins, SCL and SDA, should not exceed the absolute maximum ratings, irrespective of $V_{CC}$.

**Table 3. RELIABILITY CHARACTERISTICS**

| Symbol | Parameter | Min | Units |
|---|---|---|---|
| $N_{END}$ (Note 2) | Endurance | 1,000,000 | Write Cycles (Note 3) |
| $T_{DR}$ (Note 2) | Data Retention | 100 | Years |

2. $T_A$ = 25°C
3. A Write Cycle refers to writing a Byte or a Page.

**Table 4. D.C. OPERATING CHARACTERISTICS** ($V_{CC}$ = 1.7 V to 5.5 V, $T_A$ = −40°C to +125°C, unless otherwise specified.*)

| Symbol | Parameter | Test Conditions | | Min | Max | Units |
|---|---|---|---|---|---|---|
| $I_{CCR}$ | Read Current | Read, $f_{SCL}$ = 1 MHz | | | 0.3 | mA |
| $I_{CCW}$ | Write Current | Write | | | 0.5 | mA |
| $I_{SB}$ | Standby Current | All I/O Pins at GND or $V_{CC}$ | $T_A$ = −40°C to +85°C | | 1 | μA |
| | | | $T_A$ = −40°C to +125°C | | 2 | |
| $I_L$ | I/O Pin Leakage | Pin at GND or $V_{CC}$ | | | 2 | μA |
| $V_{IL1}$ | Input Low Voltage | 2.2 V ≤ $V_{CC}$ ≤ 5.5 V | | −0.5 | 0.3 $V_{CC}$ | V |
| $V_{IL2}$ | Input Low Voltage | 1.7 V ≤ $V_{CC}$ < 2.2 V | | −0.5 | 0.2 $V_{CC}$ | V |
| $V_{IH1}$ | Input High Voltage | 2.2 V ≤ $V_{CC}$ ≤ 5.5 V | | 0.7 $V_{CC}$ | $V_{CC}$ + 0.5 | V |
| $V_{IH2}$ | Input High Voltage | 1.7 V ≤ $V_{CC}$ < 2.2 V | | 0.8 $V_{CC}$ | $V_{CC}$ + 0.5 | V |
| $V_{OL1}$ | Output Low Voltage | $V_{CC}$ ≥ 2.2 V, $I_{OL}$ = 6.0 mA | | | 0.4 | V |
| $V_{OL2}$ | Output Low Voltage | $V_{CC}$ < 2.2 V, $I_{OL}$ = 2.0 mA | | | 0.2 | V |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*$V_{CC(min)}$ = 1.6 V for Read operations, $T_A$ = −20°C to +85°C.

**Table 5. PIN IMPEDANCE CHARACTERISTICS** $V_{CC}$ = 1.7 V to 5.5 V, $T_A$ = −40°C to +125°C, unless otherwise specified.*)

| Symbol | Parameter | Conditions | Max | Units |
|---|---|---|---|---|
| $C_{IN}$ (Note 4) | SDA I/O Pin Capacitance | $V_{IN}$ = 0 V | 8 | pF |
| $C_{IN}$ (Note 4) | Input Capacitance (other pins) | $V_{IN}$ = 0 V | 6 | pF |
| $I_{WP}$ (Note 5) | WP Input Current | $V_{IN} < V_{IH}$, $V_{CC}$ = 5.5 V | 50 | μA |
| | | $V_{IN} < V_{IH}$, $V_{CC}$ = 3.3 V | 35 | |
| | | $V_{IN} < V_{IH}$, $V_{CC}$ = 1.7 V | 25 | |
| | | $V_{IN} > V_{IH}$ | 2 | |

4. These parameters are tested initially and after a design or process change that affects the parameter according to appropriate AEC−Q100 and JEDEC test methods.
5. When not driven, the WP pin is pulled down to GND internally. For improved noise immunity, the internal pull−down is relatively strong; therefore the external driver must be able to supply the pull−down current when attempting to drive the input HIGH. To conserve power, as the input level exceeds the trip point of the CMOS input buffer (~ 0.5 x $V_{CC}$), the strong pull−down reverts to a weak current source.

*$V_{CC(min)}$ = 1.6 V for Read operations, $T_A$ = −20°C to +85°C.

**Table 6. A.C. CHARACTERISTICS** $V_{CC}$ = 1.7 V to 5.5 V, $T_A$ = −40°C to +125°C, unless otherwise specified.*) (Note 6)

| Symbol | Parameter | Standard | | Fast | | Fast−Plus | | Units |
|---|---|---|---|---|---|---|---|---|
| | | Min | Max | Min | Max | Min | Max | |
| $F_{SCL}$ | Clock Frequency | | 100 | | 400 | | 1,000 | kHz |
| $t_{HD:STA}$ | START Condition Hold Time | 4 | | 0.6 | | 0.26 | | μs |
| $t_{LOW}$ | Low Period of SCL Clock | 4.7 | | 1.3 | | 0.50 | | μs |
| $t_{HIGH}$ | High Period of SCL Clock | 4 | | 0.6 | | 0.26 | | μs |
| $t_{SU:STA}$ | START Condition Setup Time | 4.7 | | 0.6 | | 0.26 | | μs |
| $t_{HD:DAT}$ | Data In Hold Time | 0 | | 0 | | 0 | | μs |
| $t_{SU:DAT}$ | Data In Setup Time | 250 | | 100 | | 50 | | ns |
| $t_R$ (Note 7) | SDA and SCL Rise Time | | 1,000 | | 300 | | 120 | ns |
| $t_F$ (Note 7) | SDA and SCL Fall Time | | 300 | | 300 | | 120 | ns |
| $t_{SU:STO}$ | STOP Condition Setup Time | 4 | | 0.6 | | 0.26 | | μs |
| $t_{BUF}$ | Bus Free Time Between STOP and START | 4.7 | | 1.3 | | 0.5 | | μs |
| $t_{AA}$ | SCL Low to Data Out Valid | | 3.5 | | 0.9 | | 0.45 | μs |
| $t_{DH}$ (Note 7) | Data Out Hold Time | 100 | | 100 | | 50 | | ns |
| $T_i$ (Note 7) | Noise Pulse Filtered at SCL and SDA Inputs | | 50 | | 50 | | 50 | ns |
| $t_{SU:WP}$ | WP Setup Time | 0 | | 0 | | 0 | | μs |
| $t_{HD:WP}$ | WP Hold Time | 2.5 | | 2.5 | | 1 | | μs |
| $t_{WR}$ | Write Cycle Time | | 4 | | 4 | | 4 | ms |
| $t_{PU}$ (Notes 7, 8) | Power-up to Ready Mode | | 0.35 | | 0.35 | | 0.35 | ms |

6. Test conditions according to “A.C. Test Conditions” table.
7. Tested initially and after a design or process change that affects this parameter.
8. $t_{PU}$ is the delay between the time $V_{CC}$ is stable and the device is ready to accept commands.

*$V_{CC(min)}$ = 1.6 V for Read operations, $T_A$ = −20°C to +85°C.

**Table 7. A.C. TEST CONDITIONS**

| | |
|---|---|
| Input Levels | 0.2 x $V_{CC}$ to 0.8 x $V_{CC}$ for $V_{CC} \geq$ 2.2 V<br>0.15 x $V_{CC}$ to 0.85 x $V_{CC}$ for $V_{CC}$ < 2.2 V |
| Input Rise and Fall Times | ≤ 50 ns |
| Input Reference Levels | 0.3 x $V_{CC}$, 0.7 x $V_{CC}$ |
| Output Reference Levels | 0.3 x $V_{CC}$, 0.7 x $V_{CC}$ |
| Output Load | Current Source: $I_{OL}$ = 6 mA ($V_{CC} \geq$ 2.2 V); $I_{OL}$ = 2 mA ($V_{CC}$ < 2.2 V); $C_L$ = 100 pF |

## Power−On Reset (POR)

Each NV24C16LV incorporates Power−On Reset (POR) circuitry which protects the internal logic against powering up in the wrong state.

A NV24C16LV device will power up into Standby mode after $V_{CC}$ exceeds the POR trigger level and will power down into Reset mode when $V_{CC}$ drops below the POR trigger level. This bi−directional POR feature protects the device against ‘brown−out’ failure following a temporary loss of power.

## Pin Description

**SCL**: The Serial Clock input pin accepts the Serial Clock generated by the Master.

**SDA**: The Serial Data I/O pin receives input data and transmits data stored in EEPROM. In transmit mode, this pin is open drain. Data is acquired on the positive edge, and is delivered on the negative edge of SCL.

**WP**: The Write Protect input pin inhibits all write operations, when pulled HIGH. When not driven, this pin is pulled LOW internally.

## Functional Description

The NV24C16LV supports the Inter−Integrated Circuit ($I^2C$) Bus data transmission protocol, which defines a device that sends data to the bus as a transmitter and a device receiving data as a receiver. Data flow is controlled by a Master device, which generates the serial clock and all START and STOP conditions. The NV24C16LV acts as a Slave device. Master and Slave alternate as either transmitter or receiver.

### $I^2C$ Bus Protocol

The $I^2C$ bus consists of two ‘wires’, SCL and SDA. The two wires are connected to the $V_{CC}$ supply via pull−up resistors. Master and Slave devices connect to the 2−wire bus via their respective SCL and SDA pins. The transmitting device pulls down the SDA line to ‘transmit’ a ‘0’ and releases it to ‘transmit’ a ‘1’.

Data transfer may be initiated only when the bus is not busy (see AC Characteristics).

During data transfer, the SDA line must remain stable while the SCL line is high. An SDA transition while SCL is high will be interpreted as a START or STOP condition (Figure 2). The START condition precedes all commands. It consists of a HIGH to LOW transition on SDA while SCL is HIGH. The START acts as a ‘wake−up’ call to all receivers. Absent a START, a Slave will not respond to commands. The STOP condition completes all commands. It consists of a LOW to HIGH transition on SDA while SCL is HIGH.

***NOTE:*** *The I/O pins of NV24C16LV do not obstruct the SCL and SDA lines if the VCC supply is switched off. During power−up, the SCL and SDA pins (connected with pull−up resistors to VCC) will follow the VCC monotonically from VSS (0 V) to nominal VCC value, regardless of pull−up resistor value. The delta between the VCC and the instantaneous voltage levels during power ramping will be determined by the relation between bus time constant (determined by pull−up resistance and bus capacitance) and actual VCC ramp rate.*

### Device Addressing

The Master initiates data transfer by creating a START condition on the bus. The Master then broadcasts an 8−bit serial Slave address. For normal Read/Write operations, the first 4 bits of the Slave address are fixed at 1010 (Ah). The next 3 bits are used as programmable address bits when cascading multiple devices and/or as internal address bits. The last bit of the slave address, R/W, specifies whether a Read (1) or Write (0) operation is to be performed. The 3 address space extension bits are assigned as illustrated in Figure 3. $a_{10}$, $a_9$ and $a_8$ are internal address bits.

### Acknowledge

After processing the Slave address, the Slave responds with an acknowledge (ACK) by pulling down the SDA line during the 9th clock cycle (Figure 4). The Slave will also acknowledge the address byte and every data byte presented in Write mode. In Read mode the Slave shifts out a data byte, and then releases the SDA line during the $9^{th}$ clock cycle. As long as the Master acknowledges the data, the Slave will continue transmitting. The Master terminates the session by not acknowledging the last data byte (NoACK) and by issuing a STOP condition. Bus timing is illustrated in Figure 5.

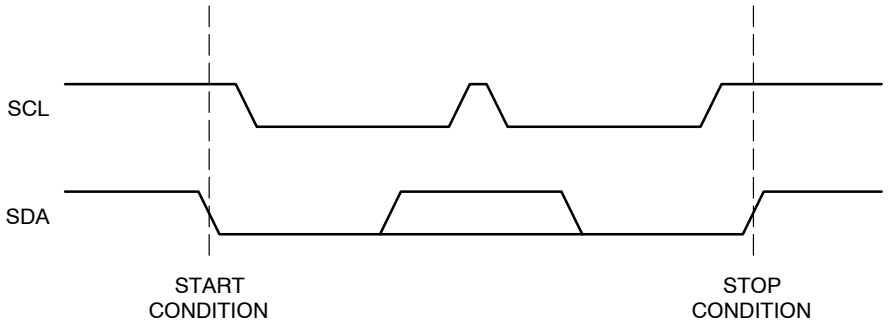



**Figure 2. Start/Stop Timing**

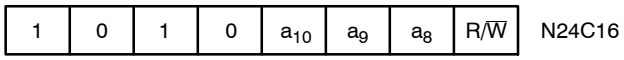



**Figure 3. Slave Address Bits**

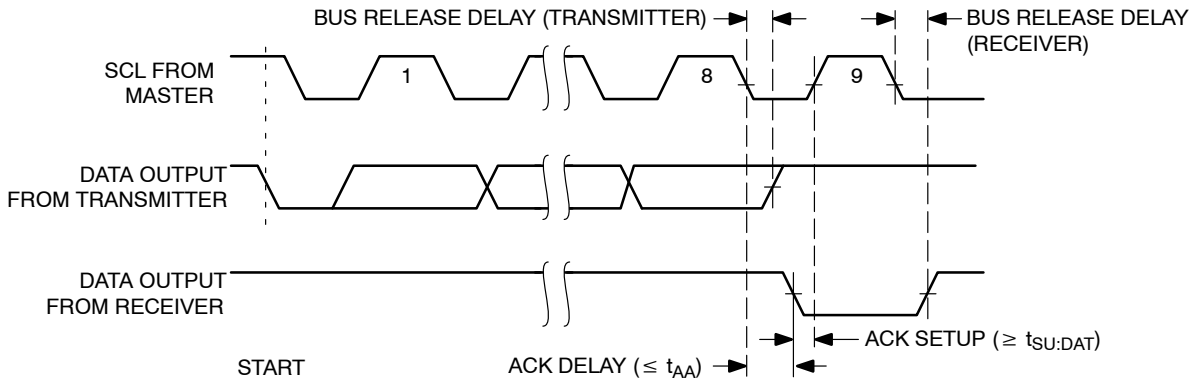



**Figure 4. Acknowledge Timing**

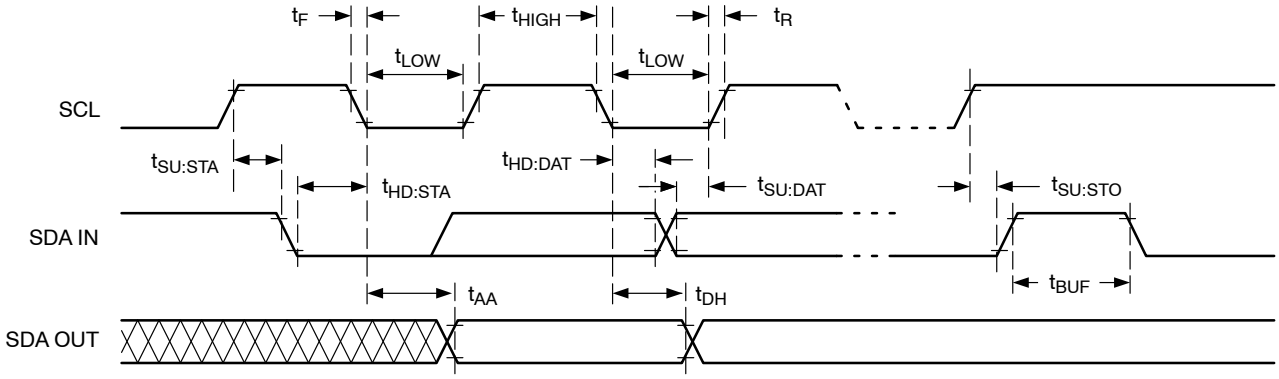



**Figure 5. Bus Timing**

## WRITE OPERATIONS

### Byte Write

In Byte Write mode, the Master sends the START condition and the Slave address with the R/W bit set to zero to the Slave. After the Slave generates an acknowledge, the Master sends the byte address that is to be written into the address pointer of the NV24C16LV. After receiving another acknowledge from the Slave, the Master transmits the data byte to be written into the addressed memory location. The NV24C16LV device will acknowledge the data byte and the Master generates the STOP condition, at which time the device begins its internal Write cycle to nonvolatile memory (Figure 6). While this internal cycle is in progress ($t_{WR}$), the SDA output will be tri−stated and the NV24C16LV will not respond to any request from the Master device (Figure 7).

### Page Write

The NV24C16LV writes up to 16 bytes of data in a single write cycle, using the Page Write operation (Figure 8). The Page Write operation is initiated in the same manner as the Byte Write operation, however instead of terminating after the data byte is transmitted, the Master is allowed to send up to fifteen additional bytes. After each byte has been transmitted the NV24C16LV will respond with an acknowledge and internally increments the four low order address bits. The high order bits that define the page address remain unchanged. If the Master transmits more than sixteen bytes prior to sending the STOP condition, the address counter ‘wraps around’ to the beginning of page and previously transmitted data will be overwritten. Once all sixteen bytes are received and the STOP condition has been sent by the Master, the internal Write cycle begins. At this point all received data is written to the NV24C16LV in a single write cycle.

### Acknowledge Polling

The acknowledge (ACK) polling routine can be used to take advantage of the typical write cycle time. Once the stop condition is issued to indicate the end of the host’s write operation, the NV24C16LV initiates the internal write cycle. The ACK polling can be initiated immediately. This involves issuing the start condition followed by the slave address for a write operation. If the NV24C16LV is still busy with the write operation, NoACK will be returned. If the NV24C16LV has completed the internal write operation, an ACK will be returned and the host can then proceed with the next read or write operation.

### Hardware Write Protection

With the WP pin held HIGH, the entire memory is protected against Write operations. If the WP pin is left floating or is grounded, it has no impact on the operation of the NV24C16LV. The state of the WP pin is strobed on the last falling edge of SCL immediately preceding the first data byte (Figure 9). If the WP pin is HIGH during the strobe interval, the NV24C16LV will not acknowledge the data byte and the Write request will be rejected.

### Delivery State

The NV24C16LV is shipped erased, i.e., all bytes are FFh.

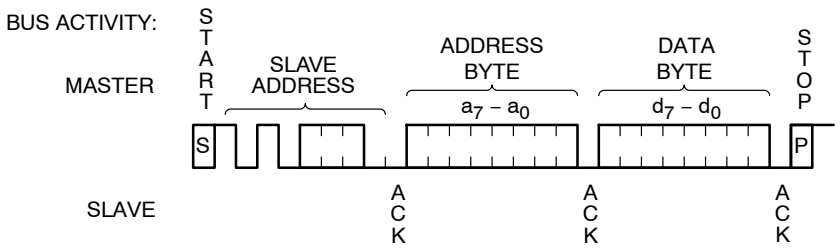



**Figure 6. Byte Write Sequence**

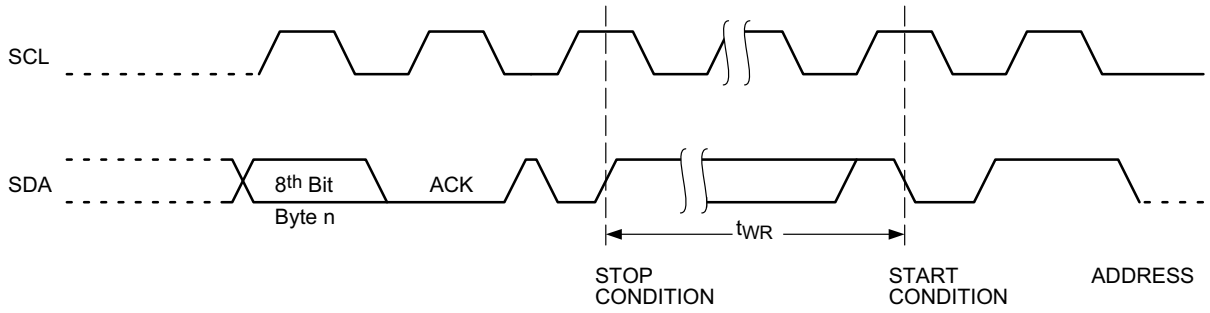



**Figure 7. Write Cycle Timing**

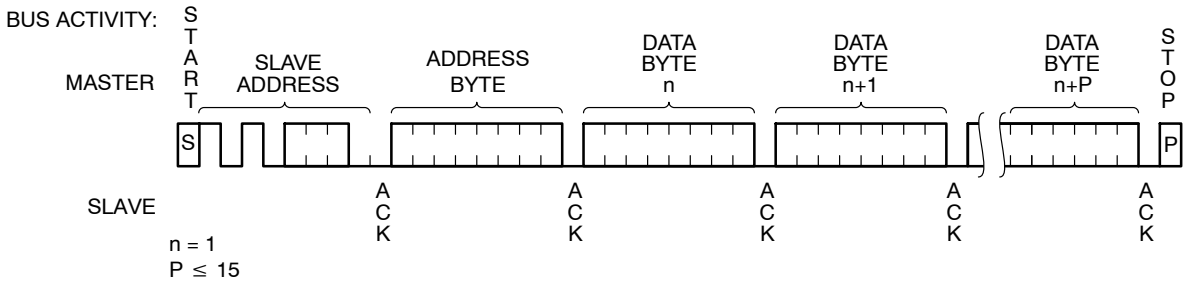



**Figure 8. Page Write Sequence**

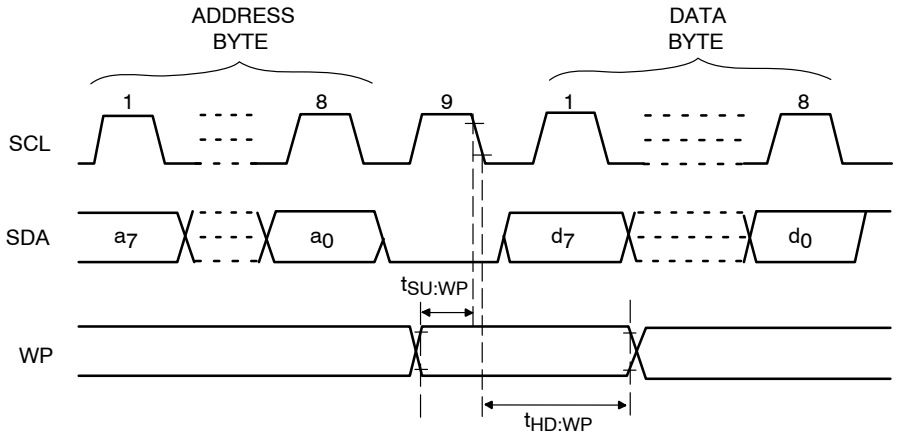



**Figure 9. WP Timing**

## READ OPERATIONS

### Immediate Read

Upon receiving a Slave address with the R/W bit set to '1', the NV24C16LV will interpret this as a request for data residing at the current byte address in memory. The NV24C16LV will acknowledge the Slave address, will immediately shift out the data residing at the current address, and will then wait for the Master to respond. If the Master does not acknowledge the data (NoACK) and then follows up with a STOP condition (Figure 10), the NV24C16LV returns to Standby mode.

### Selective Read

Selective Read operations allow the Master device to select at random any memory location for a read operation. The Master device first performs a 'dummy' write operation by sending the START condition, slave address and byte address of the location it wishes to read. After the NV24C16LV acknowledges the byte address, the Master device resends the START condition and the slave address, this time with the R/W bit set to one. The NV24C16LV then responds with its acknowledge and sends the requested data byte. The Master device does not acknowledge the data (NoACK) but will generate a STOP condition (Figure 11).

### Sequential Read

If during a Read session, the Master acknowledges the 1st data byte, then the NV24C16LV will continue transmitting data residing at subsequent locations until the Master responds with a NoACK, followed by a STOP (Figure 12). In contrast to Page Write, during Sequential Read the address count will automatically increment to and then wrap−around at end of memory (rather than end of page).

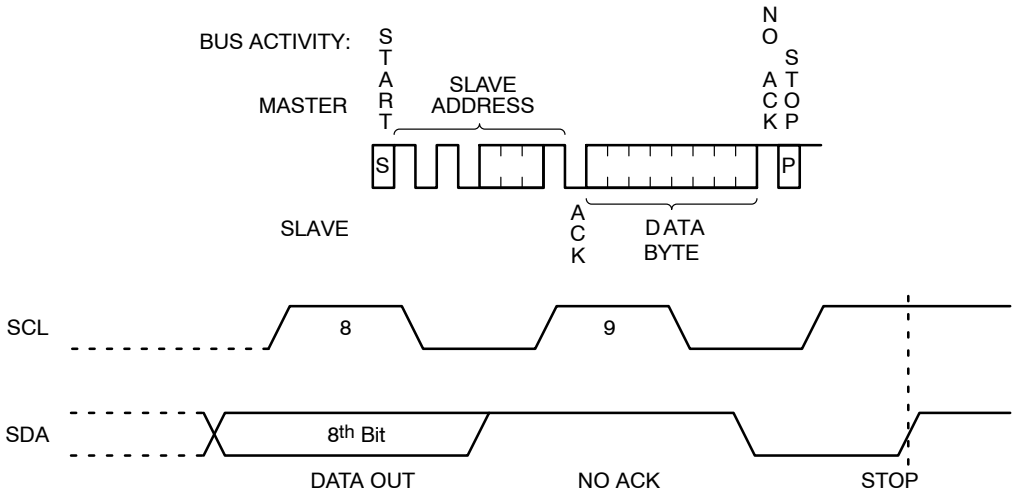



**Figure 10. Immediate Read Sequence and Timing**

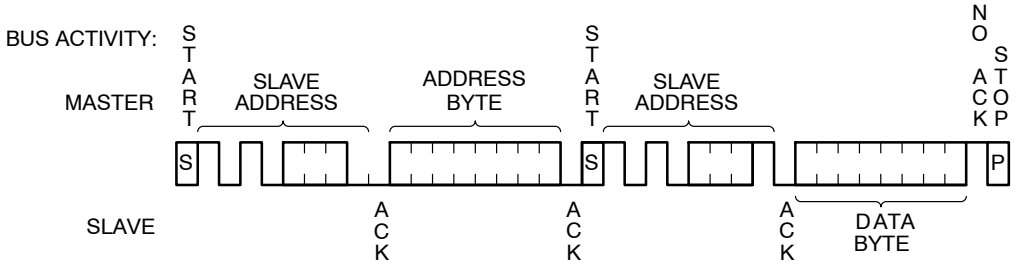



**Figure 11. Selective Read Sequence**

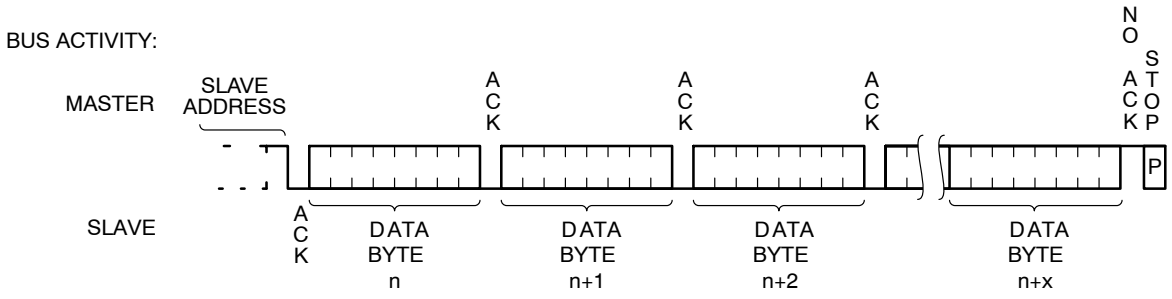



**Figure 12. Sequential Read Sequence**

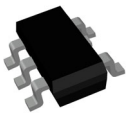
## ORDERING INFORMATION

| OPN | Density (Kb) | Package Type | Temperature Range | Shipping |
|---|---|---|---|---|
| NV24C16UVLT2G | 16 | US−8 | V = Automotive Grade 1 (−40°C to +125°C) | Tape & Reel, 2,000 Units / Reel |
| NV24C16MUW3VLTBG | 16 | UDFN8 Wettable Flank | V = Automotive Grade 1 (−40°C to +125°C) | Tape & Reel, 3,000 Units / Reel |
| NV24C16DWVLT3G | 16 | SOIC−8 | V = Automotive Grade 1 (−40°C to +125°C) | Tape & Reel, 3,000 Units / Reel |
| NV24C16DTVLT3G | 16 | TSSOP−8 | V = Automotive Grade 1 (−40°C to +125°C) | Tape & Reel, 3,000 Units / Reel |
| NV24C16SNVLT3G* | 16 | TSOP−5 | V = Automotive Grade 1 (−40°C to +125°C) | Tape & Reel, 3,000 Units / Reel |

9. All packages are RoHS−compliant (Lead−free, Halogen−free).
10. For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

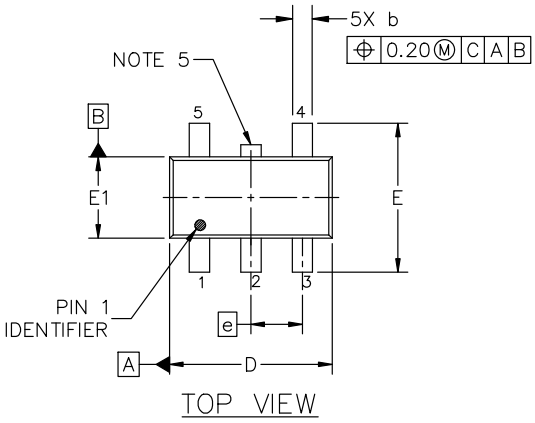
*Product in development.

**onsemi** is licensed by Philips Corporation to carry the $I^2C$ Bus Protocol.

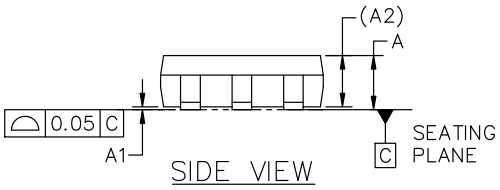


**TSOP−5 3.00x1.50x0.95, 0.95P**
CASE 483
ISSUE P

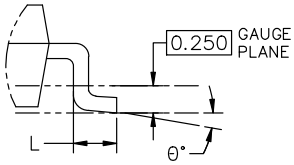
DATE 01 APR 2024



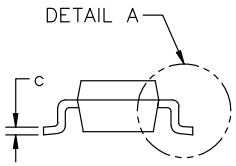

TOP VIEW




SIDE VIEW




DETAIL "A"
SCALE 2:1



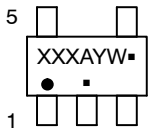

END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES).
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

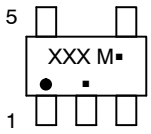
| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | 0.900 | 1.000 | 1.100 |
| A1 | 0.010 | 0.055 | 0.100 |
| A2 | | 0.950 REF. | |
| b | 0.250 | 0.375 | 0.500 |
| c | 0.100 | 0.180 | 0.260 |
| D | 2.850 | 3.000 | 3.150 |
| E | 2.500 | 2.750 | 3.000 |
| E1 | 1.350 | 1.500 | 1.650 |
| e | | 0.950 BSC | |
| L | 0.200 | 0.400 | 0.600 |
| θ | 0° | 5° | 10° |

**GENERIC**
**MARKING DIAGRAM***




**Analog**

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

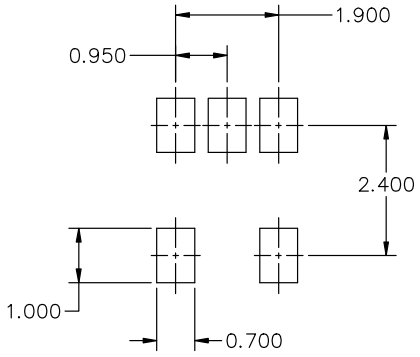



**Discrete/Logic**

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.




RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98ARB18753C** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| **DESCRIPTION:** | **TSOP−5 3.00x1.50x0.95, 0.95P** | **PAGE 1 OF 1** |

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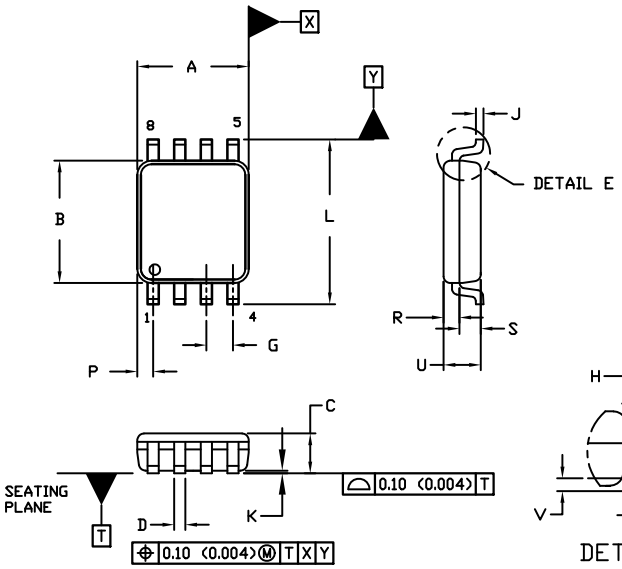
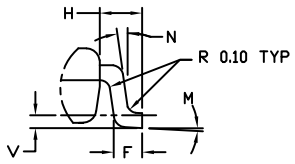
SCALE 4 :1

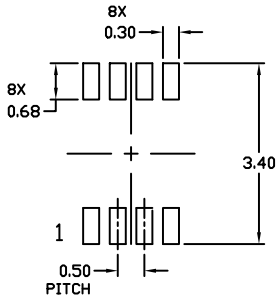
**US8**
CASE 493
ISSUE F

DATE 01 SEP 2021




DETAIL E




RECOMMENDED *
MOUNTING FOOTPRINT

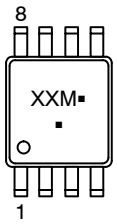
* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION, OR GATE BURR. MOLD FLASH, PROTRUSION, OR GATE BURR SHALL NOT EXCEED 0.14 (0.0055") PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH AND PROTRUSION SHALL NOT EXCEED 0.14 (0.0055") PER SIDE.
5. LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076–0.0203 MM (0.003–0.008").
6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 MM (0.002").

| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM | MIN. | MAX. | MIN. | MAX. |
| A | 1.90 | 2.10 | 0.075 | 0.083 |
| B | 2.20 | 2.40 | 0.087 | 0.094 |
| C | 0.60 | 0.90 | 0.024 | 0.035 |
| D | 0.17 | 0.25 | 0.007 | 0.010 |
| F | 0.20 | 0.35 | 0.008 | 0.014 |
| G | 0.50 BSC | | 0.020 BSC | |
| H | 0.40 REF | | 0.016 REF | |
| J | 0.10 | 0.18 | 0.004 | 0.007 |
| K | 0.00 | 0.10 | 0.000 | 0.004 |
| L | 3.00 | 3.25 | 0.118 | 0.128 |
| M | 0° | 6° | 0° | 6° |
| N | 0° | 10° | 0° | 10° |
| P | 0.23 | 0.34 | 0.010 | 0.013 |
| R | 0.23 | 0.33 | 0.009 | 0.013 |
| S | 0.37 | 0.47 | 0.015 | 0.019 |
| U | 0.60 | 0.80 | 0.024 | 0.031 |
| V | 0.12 BSC | | 0.005 BSC | |

## GENERIC MARKING DIAGRAM*




XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

| | | | |
|---|---|---|---|
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| **DESCRIPTION:** | **US8** | | **PAGE 1 OF 1** |

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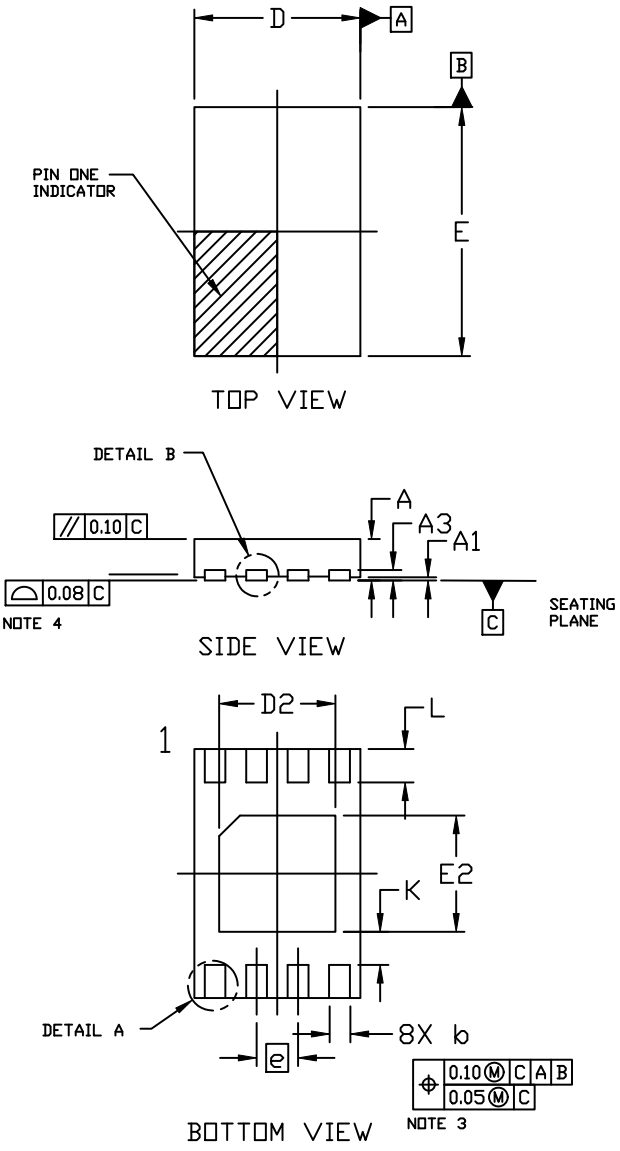
**UDFN8 2x3, 0.5P**
CASE 517DH
ISSUE A

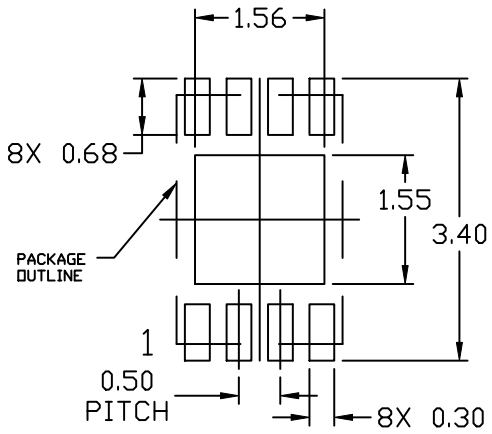
**SCALE 2:1**

DATE 10 DEC 2020




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.25MM FROM THE TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

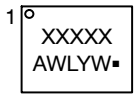
| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN. | NOM. | MAX. |
| A | 0.45 | 0.50 | 0.55 |
| A1 | 0.00 | --- | 0.05 |
| A3 | 0.13 REF | | |
| b | 0.20 | 0.25 | 0.30 |
| D | 1.90 | 2.00 | 2.10 |
| D2 | 1.30 | 1.40 | 1.50 |
| E | 2.90 | 3.00 | 3.10 |
| E2 | 1.30 | 1.40 | 1.50 |
| e | 0.50 BSC | | |
| K | 0.40 REF | | |
| L | 0.30 | 0.40 | 0.50 |




RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC MARKING DIAGRAM***




| | |
|---|---|
| XXXXX | = Specific Device Code |
| A | = Assembly Location |
| WL | = Wafer Lot |
| Y | = Year |
| W | = Work Week |
| ▪ | = Pb−Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON06579G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **UDFN8 2X3, 0.5P** | **PAGE 1 OF 1** |

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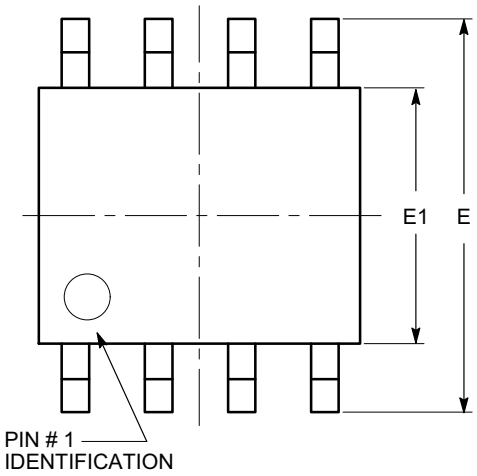
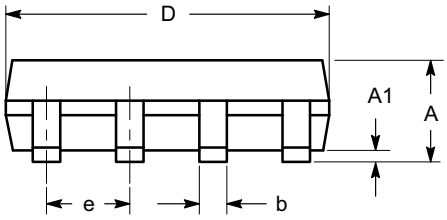
**SOIC−8, 150 mils**
CASE 751BD
ISSUE O

DATE 19 DEC 2008

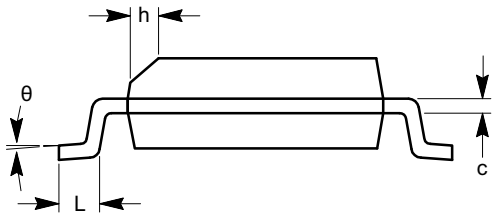



**TOP VIEW**

| SYMBOL | MIN | NOM | MAX |
|---|---|---|---|
| A | 1.35 | | 1.75 |
| A1 | 0.10 | | 0.25 |
| b | 0.33 | | 0.51 |
| c | 0.19 | | 0.25 |
| D | 4.80 | | 5.00 |
| E | 5.80 | | 6.20 |
| E1 | 3.80 | | 4.00 |
| e | 1.27 BSC | | |
| h | 0.25 | | 0.50 |
| L | 0.40 | | 1.27 |
| θ | 0º | | 8º |




**SIDE VIEW**




**END VIEW**

**Notes:**
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MS-012.

| | | | |
|---|---|---|---|
| **DOCUMENT NUMBER:** | **98AON34272E** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | |
| **DESCRIPTION:** | **SOIC−8, 150 MILS** | | **PAGE 1 OF 1** |

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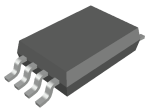
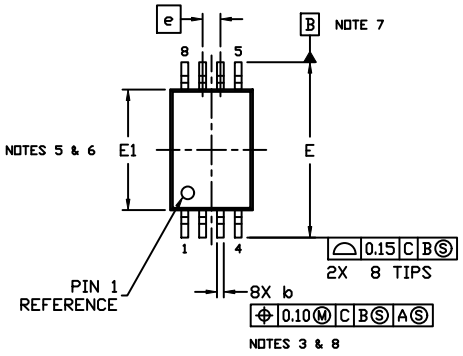
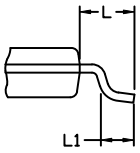


**TSSOP8, 4.4x3.0, 0.65P**
CASE 948AL
ISSUE A

DATE 20 MAY 2022



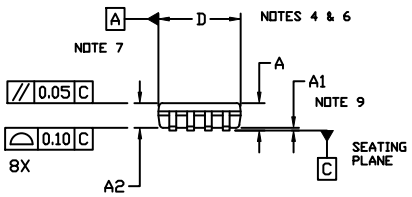

TOP VIEW



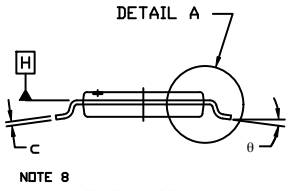

DETAIL A

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5, 2009..
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL NOT BE 0.15 IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE.
5. DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 PER SIDE.
6. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM. DIMENSIONS D AND E1 ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM PLANE H.
7. DATUMS A AND B ARE TO BE DETERMINED AT DATUM H.
8. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.10 AND 0.25 FROM THE LEAD TIP..
9. A1 IS DEFINED AS THE LOWEST VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY..



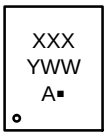

SIDE VIEW




END VIEW

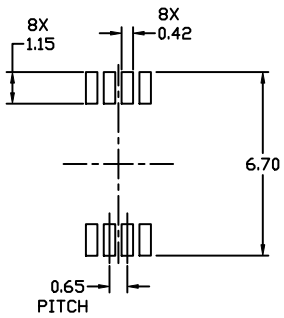
| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 1.20 |
| A1 | 0.05 | --- | 0.15 |
| A2 | 0.80 | 0.90 | 1.05 |
| b | 0.19 | --- | 0.30 |
| c | 0.09 | --- | 0.20 |
| D | 2.90 | 3.00 | 3.10 |
| E | 6.30 | 6.40 | 6.50 |
| E1 | 4.30 | 4.40 | 4.50 |
| e | 0.65 BSC | | |
| L | 1.00 REF | | |
| L1 | 0.50 | 0.60 | 0.70 |
| θ | 0° | --- | 8° |

## GENERIC MARKING DIAGRAM*




XXX = Specific Device Code
Y = Year
WW = Work Week
A = Assembly Location
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.




RECOMMENDED
MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | | |
|---|---|---|---|
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| **DESCRIPTION:** | **TSSOP8, 4.4X3.0, 0.65P** | | **PAGE 1 OF 1** |

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